## Amendments to the Claims

Claim 1 (currently amended): A reaction chamber for processing a substrate wafer, comprising:

a wafer holder for receiving the substrate wafer to be processed;

a convection plate disposed above said wafer holder, said convection plate suppressing convective movements over the substrate wafer;

a gas distributor plate disposed on a side face of the reaction chamber, said gas distributor plate distributing process and purge gases which flow in, said gas distributor plate having a surface and a plurality of gas outlet openings formed therein distributed over said surface; and

a flow plate disposed on said gas distributor plate and extending substantially in a plane perpendicular to said gas distributor plate.

Claim 2 (original): The reaction chamber according to claim 1, wherein said flow plate is disposed approximately at a level of said convection plate on said gas distributor plate.

Claim 3 (original): The reaction chamber according to claim 2, wherein said flow plate extends right up to said convection plate.

Claim 4 (original): The reaction chamber according to claim 1, wherein said flow plate has a chamber-internal edge with a profile matched to a shape of said convection plate, in order to achieve a uniform distance between said convection plate and said flow plate.

Claim 5 (cancelled).

Claim 6 (currently amendment): The reaction chamber according to claim  $\frac{5}{2}$ , wherein said gas distributor plate has said gas outlet openings disposed only below a level of said flow plate.

Claim 7 (currently amended): The reaction chamber according to claim 1, wherein A reaction chamber for processing a substrate wafer, comprising:

a wafer holder for receiving the substrate wafer to be processed;

a convection plate disposed above said wafer holder, said convection plate suppressing convective movements over the substrate wafer;

a gas distributor plate disposed on a side face of the reaction chamber, said gas distributor plate distributing process and purge gases which flow in; and

a flow plate disposed on said gas distributor plate and extending substantially in a plane perpendicular to said gas distributor plate;

at least one of said gas distributor plate and said flow plate is being formed of quartz.

Claim 8 (currently amended): The reaction chamber according to claim 1, wherein A reaction chamber for processing a substrate wafer, comprising:

a wafer holder for receiving the substrate wafer to be processed;

a convection plate disposed above said wafer holder, said convection plate suppressing convective movements over the substrate wafer;

a gas distributor plate disposed on a side face of the reaction chamber, said gas distributor plate distributing process and purge gases which flow in; and

a flow plate disposed on said gas distributor plate and extending substantially in a plane perpendicular to said gas distributor plate;

said gas distributor plate and said flow plate are being produced integrally.

Claim 9 (currently amended): A method for processing a substrate wafer, which comprises the steps of:

introducing the substrate wafer into a reaction chamber with a wafer holder, a convection plate disposed above the wafer holder, a gas distributor plate disposed on a side face of the reaction chamber and having a surface and a plurality of gas outlet openings formed therein distributed over the surface, and a flow plate disposed on the gas distributor plate and extending substantially in a plane perpendicular to the gas distributor plate;

placing the substrate wafer on the wafer holder;

feeding a process gas into the reaction chamber through the gas distributor plate;

carrying out a processing step on the substrate wafer; and

purging the reaction chamber by feeding a purge gas through  $\frac{1}{4}$  the gas distributor plate.

Claim 10 (currently amended): The method according to claim 9, which comprises rotating a the wafer holder while the processing step is being carried out on the substrate wafer, and a rotation of the substrate wafer is switched off while the reaction chamber is being purged.

Claim 11 (new): The reaction chamber according to claim 1, wherein said gas distributor plate has said gas outlet openings disposed below a level of said flow plate and above a level of said flow plate.